

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4634	(361/56-58).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/20 09:55
L2	324	string near2 diodes and (electrostatic near2 discharge ESD electrostatic near3 energy electrostatic near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:56
L3	133	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:56
L4	0	(stack\$3 series) near5 cascad\$2 and 3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:56
L5	112	(stack\$3 series cascad \$2 cascod\$3) and 3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:57
L6	214	(stack\$3 series) same cascad\$2 and (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 10:17
L7	690	cascad\$3 and (shunt shunting clamp clamping trigger triggering triggered) and (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:11

L8	37	(cascaded cascade cascading) near7 stack \$2 and 7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:12
L9	2316	(array divider series string) near2 diodes and (electrostatic near2 discharge ESD electrostatic near3 energy electrostatic near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L10	0	(stack\$3 series) near5 cascad\$2 and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L11	0	cascad\$2 and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L12	6	cascad\$3 near4 (shunt shunting clamp clamping trigger triggering triggered) and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L13	5641	freescall near2 semiconductor.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:29
L14	72	(cascaded cascade cascading) and 13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:29
L15	54	Yi near2 Hsun near2 Wu.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:30

L16	11	("20030076636"   "20040110334"   "20050041346"   "20050264963"   "6327126"   "6414532" "6522511"   "6538868"   "6747857" "6867957"   "6898062").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/20 11:33
L17	8	(cascaded cascade cascading) and 15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:33
L18	182	jian near2 hsing near2 lee.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:34
L19	15	(cascaded cascade cascading) and 18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:34
L20	17302	Taiwan near2 semiconductor near2 manufacturing.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:35
L21	739	20 and (electrostatic near2 discharge ESD electrostatic near3 energy electrostatic near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:35
L22	45	(cascaded cascade cascading) and 21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:35
L23	1	(ESD near2 protection and sensor and inverter and cascaded near2 NMOS).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:38

**4/20/2009 11:39:24 AM**

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